



# CHENMKO ENTERPRISE CO.,LTD

## SURFACE MOUNT GLASS PASSIVATED HIGH EFFICIENCY SILICON RECTIFIER

VOLTAGE RANGE 50 - 1000 Volts CURRENT 1.0 Ampere

Lead free devices

HBM11PT

THRU

HBM18PT

### FEATURES

- \* For surface mounted applications
- \* Low forward voltage, high current capability
- \* Low leakage current
- \* Metallurgically bonded construction
- \* Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- \* Glass passivated junction
- \* High temperature soldering guaranteed : 260°C/10 seconds at terminals

### MECHANICAL DATA

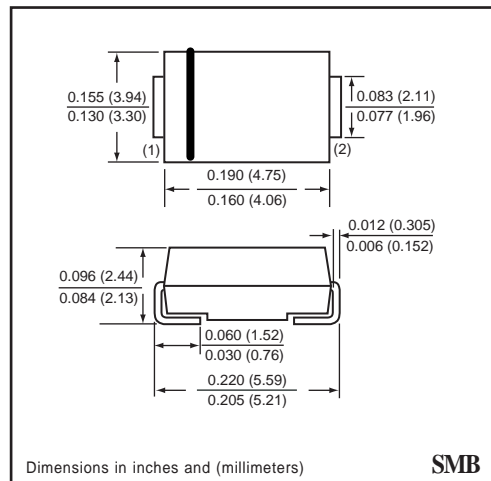
**Case:** JEDEC SMB molded plastic  
**Terminals:** Solder plated, solderable per MIL-STD-750, Method 2026  
**Polarity:** Indicated by cathode band  
**Weight:** 0.003 ounces, 0.093 gram

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.  
 Single phase, half wave, 60 Hz, resistive or inductive load.  
 For capacitive load, derate current by 20%.



SMB



Dimensions in inches and (millimeters)

SMB

### MAXIMUM RATINGS ( At TA = 25°C unless otherwise noted )

RATINGS	SYMBOL	HBM11PT	HBM12PT	HBM13PT	HBM14PT	HBM15PT	HBM16PT	HBM17PT	HBM18PT	UNITS
Maximum Recurrent Peak Reverse Voltage	VRRM	50	100	200	300	400	600	800	1000	Volts
Maximum RMS Voltage	VRMS	35	70	140	210	280	420	560	700	Volts
Maximum DC Blocking Voltage	Vdc	50	100	200	300	400	600	800	1000	Volts
Maximum Average Forward Rectified Current TL = 110°C	Io	1.0								Amps
Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	IFSM	30								Amps
Typical Junction Capacitance (Note 1)	CJ	15				12				pF
Operating and Storage Temperature Range	TJ, TSTG	-65 to +150								°C

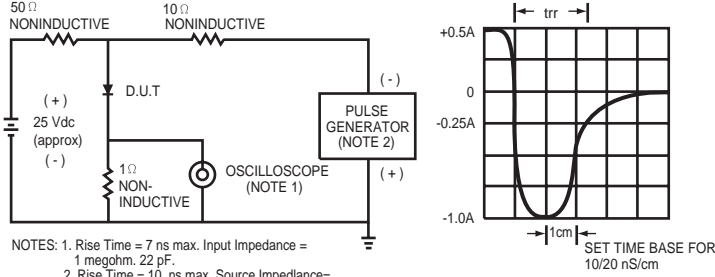
### ELECTRICAL CHARACTERISTICS ( At TA = 25°C unless otherwise noted )

CHARACTERISTICS	SYMBOL	HBM11PT	HBM12PT	HBM13PT	HBM14PT	HBM15PT	HBM16PT	HBM17PT	HBM18PT	UNITS	
Maximum Instantaneous Forward Voltage at 1.0 A DC	VF	1.0			1.3		1.5		1.7	Volts	
Maximum DC Reverse Current at Rated DC Blocking Voltage at TA = 25°C	IR	5.0								uAmps	
Maximum Full Load Reverse Current Average, Full Cycle at TA = 55°C		100								uAmps	
Maximum Reverse Recovery Time (Note 2)	trr	50					70				nSec

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 4.0 volts  
 2. Test Conditions : IF = 0.5 A, IR = -1.0 A, IRR = -0.25 A

# RATING CHARACTERISTIC CURVES ( HBM11PT THRU HBM18PT )

FIG. 1 - TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES: 1. Rise Time = 7 ns max. Input Impedance = 1 megohm, 22 pF.  
2. Rise Time = 10 ns max. Source Impedance = 50 ohms.

FIG. 2 - TYPICAL FORWARD CURRENT DERATING CURVE

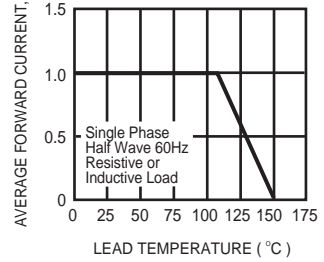


FIG. 3 - TYPICAL REVERSE CHARACTERISTICS

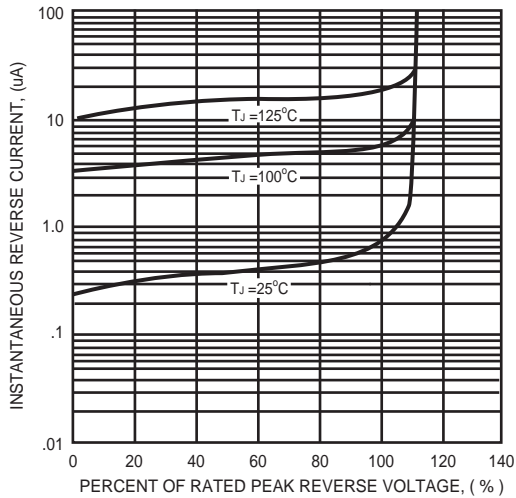


FIG. 4 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

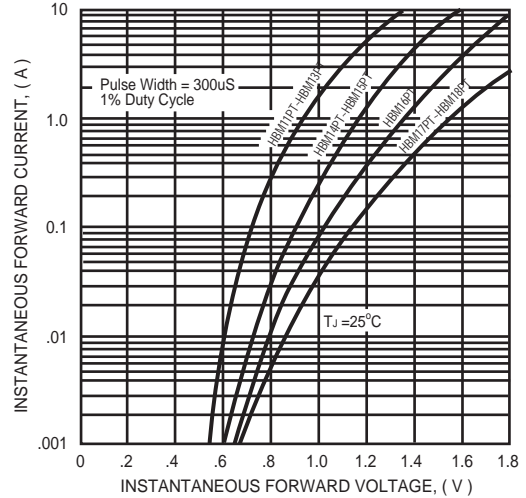


FIG. 5 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

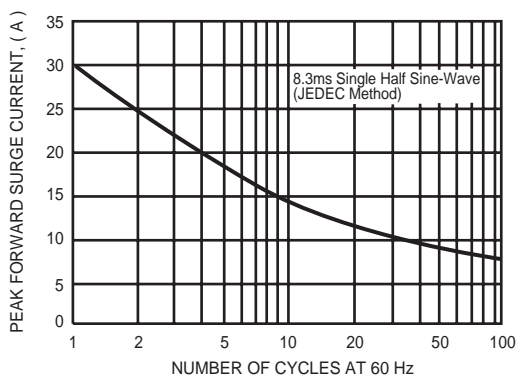


FIG. 6 - TYPICAL JUNCTION CAPACITANCE

